

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L379	171096	"hard mask" or SiN or "Silicon nitride"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:04
2	BRS	L380	22290	sacrificial	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:04
3	BRS	L381	141875 0	etch\$4 or strip\$6 or lift-off or (lift adj off)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:05
4	BRS	L376	8	sacrificial same gaps same (hard adj mask)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:05
5	BRS	L377	38	single adj plasma adj etch\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:05

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L378	4	(plasma adj etch\$4) with sacrificial with ("hard mask" or SiN or "silicon nitride") with (opening\$3 or gap\$3 or hole\$4 or trench\$4 or spac\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:05
7	BRS	L382	409	(etch\$4 or strip\$6 or lift-off or (lift adj off) near8 sacrificial near8 ("hard mask" or SiN or "Silicon nitride")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 16:05

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L10	591	(etch\$4 or remov\$4) near8 (sacrific\$6) near8 ("hard mask" or SiN or "silicon nitride" or SiON or "Silicon oxynitride")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/01/12 19:07

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L233	171378	"hard mask" or SiN or "Silicon nitride"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
2	BRS	L234	22334	sacrificial	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
3	BRS	L235	141991 5	etch\$4 or strip\$6 or lift-off or (lift adj off)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
4	BRS	L242	609	(etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
5	BRS	L243	30019	expos\$6 near4 oxide	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L244	169	((etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)) and (expos\$6 near4 oxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
7	BRS	L236	8	sacrificial same gaps same (hard adj mask)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
8	BRS	L237	38	single adj plasma adj etch\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
9	BRS	L238	4	(plasma adj etch\$4) with sacrificial with ("hard mask" or SiN or "silicon nitride") with (opening\$3 or gap\$3 or hole\$4 or trench\$4 or spac\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:40
10	BRS	L239	412	(etch\$4 or strip\$6 or lift-off or (lift adj off)) near8 sacrificial near8 ("hard mask" or SiN or "Silicon nitride")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:41
11	IS&R	L240	1	("6159821").PN.	USPAT	2004/02/13 10:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L241	12	("4389294" "4692992" "5229316" "5433794" "5712185" "5731241" "5930645" "5940717" "5994201" "5998278" "6001706" "6043133") .PN.	USPAT	2004/02/13 10:41
13	BRS	L245	103	(((etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)) and (expos\$6 near4 oxide)) and plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:41
14	BRS	L246	1	(one near2 plasma near2 etch\$6) near8 sacrificial near8 "hard mask"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:41
15	BRS	L247	245	single near2 plasma near2 etch\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/13 10:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L104	435580 3	(etch\$4 or strip\$4 or remov\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:16
2	BRS	L105	462438	sacrificial or sac or BARC or resist or resists or photoresist or photoresists	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:17
3	BRS	L106	442390 9	(gap or gaps or opening or openings or hole or holes)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:17
4	BRS	L107	539934	"hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:18
5	BRS	L108	7932	104 near8 105 near8 107	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:18

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L109	2282	108 same 106	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:19
7	BRS	L110	370827	plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:19
8	BRS	L111	454	109 same 110	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/17 15:19